Unit in mm

#### TOSHIBA PHOTOCOUPLER GaAlAs IRED + PHOTO-IC

# **TLP719**

Digital logic ground isolation Line receivers Microprocessor system interfaces Switching power supply feedback control Transistor invertors

The TOSHIBA TLP719 consists of a GaAlAs high-output light-emitting diode and a high-speed detector.

This unit is a 6-lead SDIP. The TLP719 is 50% smaller than the 8-pin DIP and meets the reinforced insulation class requirements of international safety standards. Therefore the mounting area can be reduced in equipment requiring safety standard certification.

The TLP719 has a Faraday shield integrated on the photodetector chip to provide an effective common mode noise transient immunity. Therefore this product is suitable for application in noisy environmental conditions.

: SDIP6

: 5000 Vrms (min)

- Open collector
- Package type
- Isolation voltage
- Common mode transient immunity
- Switching speed

TTL compatible

- : ±10 kV/us(min) @V<sub>CM</sub> = 400 V : t<sub>pHL/</sub> t<sub>pLH</sub> = 0.8 μs (max)
- @ I<sub>F</sub> = 16 mA , V<sub>CC</sub> = 5 V,
- $R_L$  = 1.9 k $\Omega$  , Ta = 25 °C
- Construction mechanical rating

	7.62-mm pitch standard type	10.16-mm pitch TLPXXXF type			
Creepage Distance	7.0 mm (min)	8.0 mm (min)			
Clearance	7.0 mm (min)	8.0 mm (min)			
Insulation Thickness	0.4 mm (min)	0.4 mm (min)			

- UL recognized
- Option (D4) TÜV approved

: EN60747-5-2

Certificate No. R50033433

: UL1577, File No. E67349

Maximum operating insulation voltage : 890 Vpk Highest permissible over voltage : 8000 Vpk

( Note ) When a EN60747-5-2 approved type is needed, please designate the "Option(D4)"

## PIN CONFIGURATION (Top View)



1 : ANODE

- 2 : N.C.
- 3 : CATHODE
- 4 : EMITTER (GND)
- 5 : COLLECTOR (OUTPUT)
- 6 : V<sub>CC</sub>

#### SCHEMATIC



A 0.1- $\mu$ F bypass capacitor must be connected between pins 4 and 6. (See Note 7.)



Weight: 0.26 g (typ.)

Absolute Maximum Ratings (Ta = 25 °C)

Characteristic				Rating	Unit
Forward current		(Note 1)	١ <sub>F</sub>	25	mA
	Pulse forward current	(Note 2)	I <sub>FP</sub>	50	mA
Q	Peak transient forward current	(Note 3)	I <sub>FPT</sub>	1	А
ш	Reverse voltage		V <sub>R</sub>	5	V
	Diode power dissipation	(Note 4)	PD	45	mW
	Junction temperature		Тј	125	°C
	Output current		Ι <sub>Ο</sub>	8	mA
	Peak output current		I <sub>OP</sub>	16	mA
ector	Output voltage		Vo	-0.5~20	V
Dete	Supply voltage		V <sub>CC</sub>	-0.5~30	V
	Output power dissipation	(Note 5)	PO	100	mW
	Junction Temperature		Тj	125	°C
Operating temperature range		Topr	-55~100	°C	
Storage temperature range		T <sub>stg</sub> −55~125		°C	
Lead soldering temperature (10 s)			T <sub>sol</sub> 260		°C
Isol	ation voltage (AC, 1 minute, R.H.≤ 60 %)	(Note 6)	BV <sub>S</sub> 5000		Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Derate 0.45 mA / °C above 70 °C.
- Note 2: 50% duty cycle, 1 ms pulse width. Derate 0.9 mA / °C above 70 °C.
- Note 3: Pulse width  $\leq$  1 µs, 300 pps.
- Note 4: Derate 0.8 mW / °C above 70 °C.
- Note 5: Derate 1.8 mW /  $^\circ C$  above 70  $^\circ C.$
- Note 6: Device considered a two-terminal device: pins 1, 2 and 3 paired with pins 4, 5 and 6 respectively.
- Note 7: A ceramic capacitor (0.1 μF) should be connected from pin 6 to pin 4 to stabilize the operation of the high-gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.

Electrical Characteristics (Ta = 25 °C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 16 mA		1.65	1.85	V
	Forward voltage Temperature coefficient	ΔV <sub>F</sub> / ΔTa	I <sub>F</sub> = 16 mA	_	-2	_	mV / °C
	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	—	—	10	μA
	Capacitance between terminals	CT	V <sub>F</sub> = 0 V , f = 1 MHz	—	45	—	pF
Detector	HIGH-level output current	I <sub>OH (1)</sub>	$I_{F} = 0 \text{ mA}$ , $V_{CC} = V_{O} = 5.5 \text{ V}$	_	3	500	nA
		I <sub>OH (2)</sub>	I <sub>F</sub> = 0 mA ,V <sub>CC</sub> = 30 V V <sub>O</sub> = 20 V	_	_	5	
		I <sub>ОН</sub>	I <sub>F</sub> = 0 mA ,V <sub>CC</sub> = 30 V V <sub>O</sub> = 20 V,Ta = 70 °C	_	_	50	μΑ
	HIGH-level supply current	ICCH	I <sub>F</sub> = 0 mA ,V <sub>CC</sub> = 30 V	_	0.01	1	μA
	Supply voltage	V <sub>CC</sub>	I <sub>CC</sub> = 0.01 mA	30	_	_	V
	Output voltage	VO	I <sub>O</sub> = 0.5 mA	20	—	—	V

# Coupled Electrical Characteristics (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	I <sub>O</sub> / I <sub>F</sub>	I <sub>F</sub> = 16 mA ,V <sub>CC</sub> = 4.5 V V <sub>O</sub> = 0.4 V	20	_	_	%
LOW-level output voltage	V <sub>OL</sub>	$I_{F} = 16 \text{ mA}, V_{CC} = 4.5 \text{ V}$ $I_{O} = 2.4 \text{ mA}$			0.4	V

# Isolation Characteristics (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0 V , f = 1 MHz (Note 6)	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	R.H. ≤ 60% ,V <sub>S</sub> = 500 V (Note 6)	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	BVS	AC, 1 minute	5000	-	_	V
		AC, 1 second , in oil	—	10000	_	v rms
		DC, 1 minute , in oil	—	10000	-	Vdc

## Switching Characteristics (Ta = 25 °C, V<sub>CC</sub> = 5 V)

Characteristic	Symbol	Test Cir- cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time $(H \rightarrow L)$	t <sub>pHL</sub>	- Fig1	I <sub>F</sub> = 0→ 16 mA R <sub>L</sub> = 1.9kΩ	_	_	0.8	μs
Propagation delay time $(L \rightarrow H)$	t <sub>pLH</sub>		l <sub>F</sub> = 16→ 0 mA R <sub>L</sub> = 1.9kΩ			0.8	μs
Common mode transient immunity at logic HIGH output (Note 8)	CMH	Fig2	I <sub>F</sub> = 0 mA V <sub>CM</sub> = 400 Vp–p R <sub>L</sub> = 1.9kΩ	10000	_	_	V / µs
Common mode transient immunity at logic LOW output (Note 8)	CML		I <sub>F</sub> = 16 mA V <sub>CM</sub> = 400 Vp–p R <sub>L</sub> = 1.9 kΩ	-10000	_	_	V / µs

Note 8 :  $CM_L$  is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic LOW state ( $V_O < 0.8 \text{ V}$ ).

 $CM_H$  is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic HIGH state (V<sub>O</sub> >2 V).

Figure 1. Switching Time Test Circuit



Figure 2. Common Mode Noise Immunity Test Circuit.



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0.1 L 1

3

5



tpHL

10

Load resistance  $R_L(k\Omega)$ 

30 50 100

-tpHL

tpLH

20

40

Ambient temperature Ta (°C)

60

80

100

0.<u>1</u>40

-20

0

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